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ABSTRACT OF THE DISCLOSURE

The invention is directed to an optically pumped surface-emitting semiconductor laser device having at least one radiation-generating quantum well structure and at least one pump radiation source for optically pumping the quantum well structure, whereby the pump radiation source comprises an edge-emitting semiconductor structure. The radiation-generating quantum well structure and the edge-emitting semiconductor structure are epitaxially grown on a common substrate. A very efficient and uniform optical pumping of the radiation-generating quantum well structure is advantageously possible with this monolithically produced semiconductor laser device. Methods for manufacturing inventive semiconductor laser devices are also specified.